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095001 Jifeng

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1 Broad.

1/2 active
his
or friends

creep-up height of the conductive die-bond paste at a side face of the semiconductor laser chip from a die-bond surface of the semiconductor laser chip is not more than 40 μm .

- 5 4. The semiconductor laser device according to Claim 2, wherein

the conductive die-bond paste interposed between a die-bond surface of the semiconductor laser chip and the base portion is 5 μm or lower thick.

- 10 5. The semiconductor laser device according to Claim 2, wherein

the conductive die-bond paste using a metal is silver paste.

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